

## REMARKS/ARGUMENT

Applicant responds herein the Office Action dated October 25, 2005.

Claims 1-17, 19-35 and 37 were rejected under 35 U.S.C. §102(e) as being anticipated by Basceri et al. U.S. Patent No. 6,753,618 B2. Reconsideration of the rejection is respectfully requested.

Independent claim 1 has been amended to provide, in part, for, “[a] method for manufacturing a semiconductor device, comprising a dual-stage deposition step comprising: a first stage for introducing a material gas containing an oxide of a desired metal ....” Independent claim 19 has been amended to provide, in part, for, “[a] method for manufacturing a semiconductor device having a capacitor, comprising: a dual-stage deposition step comprising: a first stage for introducing a material gas containing an oxide of a desired metal ....” Independent claim 37 has been amended to provide, in part, for, “[a] method for manufacturing a semiconductor device, comprising the steps of: a first stage for introducing a material gas containing an oxide of a desired metal ....” Antecedent basis for the amendments to independent claims 1, 19, and 37 is found in the specification, for example, on page 16, lines 6-7.

In contrast, the Examiner, in stating the basis of the rejection for independent claim 1, indicates that the material gas containing a desired metal is aluminum tetrachloride, (Office Action, page 4, paragraph 3, lines 3-4), which is not an oxide of a metal, as claimed in independent claims 1, 19, and 37.

Since claims 2-17 and 20-35 are directly or indirectly dependent upon one of independent claims 1 and 19, they are allowable over Basceri et al. for the same reasons recited above with respect to the allowability of independent claims 1, 19, and 37 over Basceri et al.

Claims 18 and 36 were rejected under 35 U.S.C. §103(a) as being unpatentable over Basceri et al. in view of Roberts et al., U.S. Patent No. 6,461,914 B2. Reconsideration of the rejection is respectfully requested.

Since claims 18 and 36 are indirectly dependent upon independent claims 1 and 19, respectively, they are allowable over Basceri et al. for the same reasons recited above with respect to the allowability of independent claims 1 and 19 over Basceri et al. With regard to Roberts et al., although it discloses a capacitor dielectric layer 50 which comprises a metal oxide,

(column 5, lines 3-11), there is no disclosure, teaching, or suggestion of a method of manufacturing a semiconductor device comprising a step of introducing a material gas containing an oxide of a desired metal, as claimed in independent claims 1, 19, and 37.

Accordingly, the Examiner is respectfully requested to reconsider the application, allow the claims as amended and pass this case to issue.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on January 24, 2006

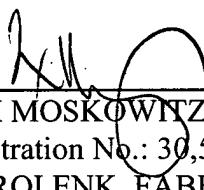
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Signature  
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Respectfully submitted,

  
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